

Welcome to **E-XFL.COM**

Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	128
Total RAM Bits	-
Number of I/O	41
Number of Gates	3000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	64-LQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/ex64-ftqg64

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Temperature Grade Offerings

Device\ Package	TQ64	TQ100
eX64	C, I, A	C, I, A
eX128	C, I, A	C, I, A
eX256	C, I, A	C, I, A

Note: C = Commercial I = Industrial A = Automotive

Speed Grade and Temperature Grade Matrix

	– F	Std	- P
С	✓	✓	✓
1		✓	✓
Α		✓	

Note: P = Approximately 30% faster than Standard

-F = Approximately 40% slower than Standard

Refer to the eX Automotive Family FPGAs datasheet for details on automotive temperature offerings.

Contact your local Microsemi representative for device availability.

Revision 10 III



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Routing Resources

Clusters and SuperClusters can be connected through the use of two innovative local routing resources called FastConnect and DirectConnect, which enable extremely fast and predictable interconnection of modules within Clusters and SuperClusters (Figure 1-4). This routing architecture also dramatically reduces the number of antifuses required to complete a circuit, ensuring the highest possible performance.

DirectConnect is a horizontal routing resource that provides connections from a C-cell to its neighboring R-cell in a given SuperCluster. DirectConnect uses a hard-wired signal path requiring no programmable interconnection to achieve its fast signal propagation time of less than 0.1 ns (–P speed grade).

FastConnect enables horizontal routing between any two logic modules within a given SuperCluster and vertical routing with the SuperCluster immediately below it. Only one programmable connection is used in a FastConnect path, delivering maximum pin-to-pin propagation of 0.3 ns (–P speed grade).

In addition to DirectConnect and FastConnect, the architecture makes use of two globally oriented routing resources known as segmented routing and high-drive routing. The segmented routing structure of Microsemi provides a variety of track lengths for extremely fast routing between SuperClusters. The exact combination of track lengths and antifuses within each path is chosen by the fully automatic place-and-route software to minimize signal propagation delays.

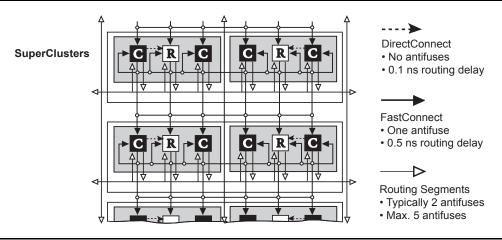


Figure 1-4 • DirectConnect and FastConnect for SuperClusters

Clock Resources

eX's high-drive routing structure provides three clock networks. The first clock, called HCLK, is hardwired from the HCLK buffer to the clock select MUX in each R-Cell. HCLK cannot be connected to combinational logic. This provides a fast propagation path for the clock signal, enabling the 3.9 ns clock-to-out (pad-to-pad) performance of the eX devices. The hard-wired clock is tuned to provide a clock skew of less than 0.1 ns worst case. If not used, the HCLK pin must be tied LOW or HIGH and must not be left floating. Figure 1-5 describes the clock circuit used for the constant load HCLK.

HCLK does not function until the fourth clock cycle each time the device is powered up to prevent false output levels due to any possible slow power-on-reset signal and fast start-up clock circuit. To activate HCLK from the first cycle, the TRST pin must be reserved in the Design software and the pin must be tied to GND on the board. (See the "TRST, I/O Boundary Scan Reset Pin" on page 1-32).

The remaining two clocks (CLKA, CLKB) are global routed clock networks that can be sourced from external pins or from internal logic signals (via the CLKINT routed clock buffer) within the eX device. CLKA and CLKB may be connected to sequential cells or to combinational logic. If CLKA or CLKB is sourced from internal logic signals, the external clock pin cannot be used for any other input and must be tied LOW or HIGH and must not float. Figure 1-6 describes the CLKA and CLKB circuit used in eX devices.



Other Architectural Features

Performance

The combination of architectural features described above enables eX devices to operate with internal clock frequencies exceeding 350 MHz for very fast execution of complex logic functions. The eX family is an optimal platform upon which the functionality previously contained in CPLDs can be integrated. eX devices meet the performance goals of gate arrays, and at the same time, present significant improvements in cost and time to market. Using timing-driven place-and-route tools, designers can achieve highly deterministic device performance.

User Security

Microsemi FuseLock advantage provides the highest level of protection in the FPGA industry against unauthorized modifications. In addition to the inherent strengths of the architecture, special security fuses that are intended to prevent internal probing and overwriting are hidden throughout the fabric of the device. They are located such that they cannot be accessed or bypassed without destroying the rest of the device, making Microsemi antifuse FPGAs highly resistant to both invasive and more subtle noninvasive attacks.

Look for this symbol to ensure your valuable IP is secure. The FuseLock Symbol on the FPGA ensures that the device is safeguarded to cryptographic attacks.



Figure 1-7 • Fuselock

For more information, refer to Implementation of Security in Microsemi Antifuse FPGAs application note.

I/O Modules

Each I/O on an eX device can be configured as an input, an output, a tristate output, or a bidirectional pin. Even without the inclusion of dedicated I/O registers, these I/Os, in combination with array registers, can achieve clock-to-out (pad-to-pad) timing as fast as 3.9 ns. I/O cells in eX devices do not contain embedded latches or flip-flops and can be inferred directly from HDL code. The device can easily interface with any other device in the system, which in turn enables parallel design of system components and reduces overall design time.

All unused I/Os are configured as tristate outputs by Microsemi's Designer software, for maximum flexibility when designing new boards or migrating existing designs. Each I/O module has an available pull-up or pull-down resistor of approximately 50 k Ω that can configure the I/O in a known state during power-up. Just shortly before V_{CCA} reaches 2.5 V, the resistors are disabled and the I/Os will be controlled by user logic.

Table 1-2 describes the I/O features of eX devices. For more information on I/Os, refer to *Microsemi eX, SX-A, and RT54SX-S I/Os* application note.

Table 1-2 • I/O Features

Function	Description
Input Buffer Threshold	• 5.0V TTL
Selection	• 3.3V LVTTL
	• 2.5V LVCMOS2
Nominal Output Drive	5.0V TTL/CMOS
	• 3.3V LVTTL
	• 2.5V LVCMOS 2
Output Buffer	"Hot-Swap" Capability
	I/O on an unpowered device does not sink current
	Can be used for "cold sparing"
	Selectable on an individual I/O basis
	Individually selectable low-slew option
Power-Up	Individually selectable pull ups and pull downs during power-up (default is to power up in tristate)
	Enables deterministic power-up of device
	V _{CCA} and V _{CCI} can be powered in any order

The eX family supports mixed-voltage operation and is designed to tolerate 5.0 V inputs in each case. A detailed description of the I/O pins in eX devices can be found in "Pin Description" on page 1-31.

Hot-Swapping

eX I/Os are configured to be hot-swappable. During power-up/down (or partial up/down), all I/Os are tristated, provided V_{CCA} ramps up within a diode drop of V_{CCI} . V_{CCA} and V_{CCI} do not have to be stable. during power-up/down, and they do not require a specific power-up or power-down sequence in order to avoid damage to the eX devices. In addition, all outputs can be programmed to have a weak resistor pull-up or pull-down for output tristate at power-up. After the eX device is plugged into an electrically active system, the device will not degrade the reliability of or cause damage to the host system. The device's output pins are driven to a high impedance state until normal chip operating conditions are reached. Please see the application note, *Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications*, which also applies to the eX devices, for more information on hot swapping.

Power Requirements

Power consumption is extremely low for the eX family due to the low capacitance of the antifuse interconnects. The antifuse architecture does not require active circuitry to hold a charge (as do SRAM or EPROM), making it the lowest-power FPGA architecture available today.

Low Power Mode

The eX family has been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated when the device enters this mode. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when returning to normal operating mode. I/Os can be driven during LP mode. For details, refer to the *Design for Low Power in Microsemi Antifuse FPGAs* application note under the section Using the LP Mode Pin on eX Devices. Clock pins should be driven either HIGH or LOW and should not float; otherwise, they will draw current and burn power. The device must be re-initialized when exiting LP mode.

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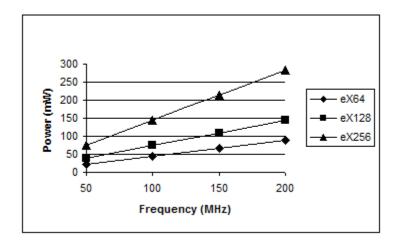
To exit the LP mode, the LP pin must be driven LOW for over 200 μs to allow for the charge pumps to power-up and device initialization can begin.

Table 1-3 illustrates the standby current of eX devices in LP mode.

Table 1-3 • Standby Power of eX Devices in LP Mode Typical Conditions, V_{CCA} , V_{CCI} = 2.5 V, T_J = 25° C

Product	Low Power Standby Current	Units
eX64	100	μΑ
eX128	111	μΑ
eX256	134	μΑ

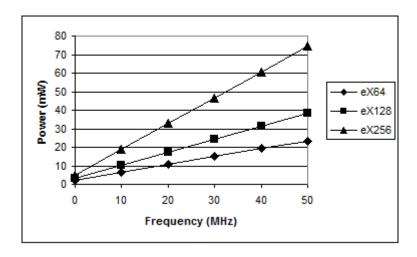
Figure 1-8 to Figure 1-11 on page 1-9 show some sample power characteristics of eX devices.



Notes:

- 1. Device filled with 16-bit counters.
- 2. VCCA, VCCI = 2.7 V, device tested at room temperature.

Figure 1-8 • eX Dynamic Power Consumption – High Frequency



Notes:

- 1. Device filled with 16-bit counters.
- 2. VCCA, VCCI = 2.7 V, device tested at room temperature.

Figure 1-9 • eX Dynamic Power Consumption – Low Frequency

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Table 1-5 describes the different configuration requirements of BST pins and their functionality in different modes.

Table 1-5 • Boundary-Scan Pin Configurations and Functions

Mode	Designer "Reserve JTAG" Selection	TAP Controller State
Dedicated (JTAG)	Checked	Any
Flexible (User I/O)	Unchecked	Test-Logic-Reset
Flexible (JTAG)	Unchecked	Any EXCEPT Test-Logic-Reset

TRST Pin

The TRST pin functions as a dedicated Boundary-Scan Reset pin when the **Reserve JTAG Test Reset** option is selected, as shown in Figure 1-12. An internal pull-up resistor is permanently enabled on the TRST pin in this mode. It is recommended to connect this pin to GND in normal operation to keep the JTAG state controller in the Test-Logic-Reset state. When JTAG is being used, it can be left floating or be driven HIGH.

When the **Reserve JTAG Test Reset** option is not selected, this pin will function as a regular I/O. If unused as an I/O in the design, it will be configured as a tristated output.

JTAG Instructions

Table 1-6 lists the supported instructions with the corresponding IR codes for eX devices.

Table 1-6 • JTAG Instruction Code

Instructions (IR4: IR0)	Binary Code	
EXTEST	00000	
SAMPLE / PRELOAD	00001	
INTEST	00010	
USERCODE	00011	
IDCODE	00100	
HIGHZ	01110	
CLAMP	01111	
Diagnostic	10000	
BYPASS	11111	
Reserved	All others	

Table 1-7 lists the codes returned after executing the IDCODE instruction for eX devices. Note that bit 0 is always "1." Bits 11-1 are always "02F", which is Microsemi SoC Products Group's manufacturer code.

Table 1-7 • IDCODE for eX Devices

Device	Revision	Bits 31-28	Bits 27-12
eX64	0	8	40B2, 42B2
eX128	0	9	40B0, 42B0
eX256	0	9	40B5, 42B5
eX64	1	А	40B2, 42B2
eX128	1	В	40B0, 42B0
eX256	1	В	40B5, 42B5



Programming

Device programming is supported through Silicon Sculptor series of programmers. In particular, Silicon Sculptor II is a compact, robust, single-site and multi-site device programmer for the PC.

With standalone software, Silicon Sculptor II allows concurrent programming of multiple units from the same PC, ensuring the fastest programming times possible. Each fuse is subsequently verified by Silicon Sculptor II to insure correct programming. In addition, integrity tests ensure that no extra fuses are programmed. Silicon Sculptor II also provides extensive hardware self-testing capability.

The procedure for programming an eX device using Silicon Sculptor II is as follows:

- 1. Load the *.AFM file
- 2. Select the device to be programmed
- 3. Begin programming

When the design is ready to go to production, Microsemi offers device volume-programming services either through distribution partners or via in-house programming from the factory.

For more details on programming eX devices, please refer to the *Programming Antifuse Devices* application note and the *Silicon Sculptor II User's Guide*.

Probing Capabilities

eX devices provide internal probing capability that is accessed with the JTAG pins. The Silicon Explorer II Diagnostic hardware is used to control the TDI, TCK, TMS and TDO pins to select the desired nets for debugging. The user simply assigns the selected internal nets in the Silicon Explorer II software to the PRA/PRB output pins for observation. Probing functionality is activated when the BST pins are in JTAG mode and the TRST pin is driven HIGH or left floating. If the TRST pin is held LOW, the TAP controller will remain in the Test-Logic-Reset state so no probing can be performed. The Silicon Explorer II automatically places the device into JTAG mode, but the user must drive the TRST pin HIGH or allow the internal pull-up resistor to pull TRST HIGH.

When you select the **Reserve Probe Pin** box, as shown in Figure 1-12 on page 1-10, the layout tool reserves the PRA and PRB pins as dedicated outputs for probing. This reserve option is merely a guideline. If the Layout tool requires that the PRA and PRB pins be user I/Os to achieve successful layout, the tool will use these pins for user I/Os. If you assign user I/Os to the PRA and PRB pins and select the **Reserve Probe Pin** option, Designer Layout will override the "Reserve Probe Pin" option and place your user I/Os on those pins.

To allow for probing capabilities, the security fuse must not be programmed. Programming the security fuse will disable the probe circuitry. Table 1-8 on page 1-13 summarizes the possible device configurations for probing once the device leaves the Test-Logic-Reset JTAG state.

Silicon Explorer II Probe

Silicon Explorer II is an integrated hardware and software solution that, in conjunction with Microsemi Designer software tools, allow users to examine any of the internal nets of the device while it is operating in a prototype or a production system. The user can probe into an eX device via the PRA and PRB pins without changing the placement and routing of the design and without using any additional resources. Silicon Explorer II's noninvasive method does not alter timing or loading effects, thus shortening the debug cycle.

Silicon Explorer II does not require re-layout or additional MUXes to bring signals out to an external pin, which is necessary when using programmable logic devices from other suppliers.

Silicon Explorer II samples data at 100 MHz (asynchronous) or 66 MHz (synchronous). Silicon Explorer II attaches to a PC's standard COM port, turning the PC into a fully functional 18-channel logic analyzer. Silicon Explorer II allows designers to complete the design verification process at their desks and reduces verification time from several hours per cycle to a few seconds.

The Silicon Explorer II tool uses the boundary scan ports (TDI, TCK, TMS and TDO) to select the desired nets for verification. The selected internal nets are assigned to the PRA/PRB pins for observation. Figure 1-13 on page 1-13 illustrates the interconnection between Silicon Explorer II and the eX device to perform in-circuit verification.

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Related Documents

Datasheet

eX Automotive Family FPGAs www.microsemi.com/soc/documents/eX Auto DS.pdf

Application Notes

 $\textit{Maximizing Logic Utilization in eX}, \ \textit{SX} \ \textit{and SX-A FPGA Devices Using CC Macros}$

www.microsemi.com/soc/documents/CC Macro AN.pdf

Implementation of Security in Microsemi Antifuse FPGAs

www.microsemi.com/soc/documents/Antifuse_Security_AN.pdf

Microsemi eX, SX-A, and RT54SX-S I/Os

www.microsemi.com/soc/documents/antifuseIO AN.pdf

Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications

www.microsemi.com/soc/documents/HotSwapColdSparing AN.pdf

Design For Low Power in Microsemi Antifuse FPGAs

www.microsemi.com/soc/documents/Low_Power_AN.pdf

Programming Antifuse Devices

www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf

User Guides

Silicon Sculptor II User's Guide
www.microsemi.com/soc/documents/SiliSculptII_Sculpt3_ug.pdf

Miscellaneous

Libero IDE flow

www.microsemi.com/soc/products/tools/libero/flow.html

2.5 V / 3.3 V /5.0 V Operating Conditions

Table 1-9 • Absolute Maximum Ratings*

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	-0.3 to +6.0	V
VCCA	DC Supply Voltage for Array	-0.3 to +3.0	V
VI	Input Voltage	-0.5 to +5.75	V
VO	Output Voltage	-0.5 to +V _{CCI}	V
T _{STG}	Storage Temperature	-65 to +150	°C

Note: *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the Recommended Operating Conditions.

Table 1-10 • Recommended Operating Conditions

Parameter	Commercial	Industrial	Units
Temperature Range*	0 to +70	-40 to +85	°C
2.5V Power Supply Range (VCCA, VCCI)	2.3 to 2.7	2.3 to 2.7	V
3.3V Power Supply Range (VCCI)	3.0 to 3.6	3.0 to 3.6	V
5.0V Power Supply Range (VCCI)	4.75 to 5.25	4.75 to 5.25	V

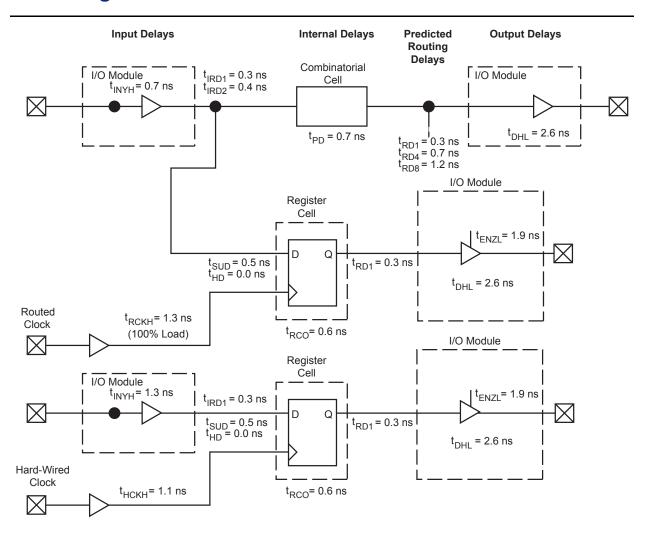
Note: *Ambient temperature (T_A) .

Table 1-11 • Typical eX Standby Current at 25°C

Product	VCCA= 2.5 V VCCI = 2.5 V	VCCA = 2.5 V VCCI = 3.3 V	VCCA = 2.5 V VCCI = 5.0 V
eX64	397 μΑ	497 μA	700 μA
eX128	696 μΑ	795 μA	1,000 μΑ
eX256	698 µA	796 µA	2,000 μΑ

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eX Timing Model



Note: Values shown for eX128-P, worst-case commercial conditions (5.0 V, 35 pF Pad Load).

Figure 1-14 • eX Timing Model

Hardwired Clock

External Setup =
$$t_{INYH} + t_{IRD1} + t_{SUD} - t_{HCKH}$$

= 0.7 + 0.3 + 0.5 - 1.1 = 0.4 ns
Clock-to-Out (Pad-to-Pad), typical
= $t_{HCKH} + t_{RCO} + t_{RD1} + t_{DHL}$
= 1.1 + 0.6 + 0.3 + 2.6 = 4.6 ns

Routed Clock

External Setup =
$$t_{INYH} + t_{IRD2} + t_{SUD} - t_{RCKH}$$

= 0.7 + 0.4 + 0.5 - 1.3= 0.3 ns
Clock-to-Out (Pad-to-Pad), typical
= $t_{RCKH} + t_{RCO} + t_{RD1} + t_{DHL}$
= 1.3+ 0.6 + 0.3 + 2.6 = 4.8 ns

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Output Buffer Delays

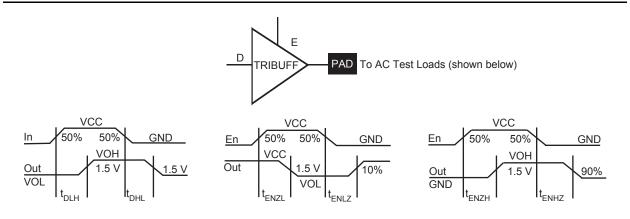


Table 1-13 • Output Buffer Delays

AC Test Loads

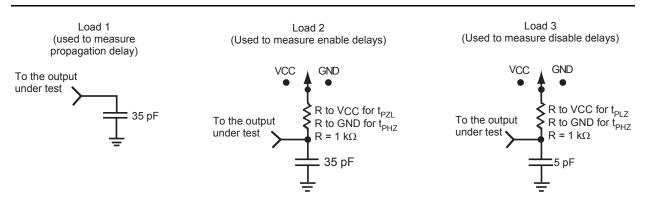


Figure 1-15 • AC Test Loads



Cell Timing Characteristics

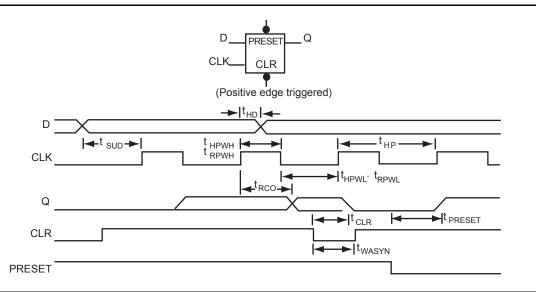


Figure 1-16 • Flip-Flops

Timing Characteristics

Timing characteristics for eX devices fall into three categories: family-dependent, device-dependent, and design-dependent. The input and output buffer characteristics are common to all eX family members. Internal routing delays are device-dependent. Design dependency means actual delays are not determined until after placement and routing of the user's design are complete. Delay values may then be determined by using the Timer utility or performing simulation with post-layout delays.

Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing critical paths. Critical nets are determined by net property assignment prior to placement and routing. Up to six percent of the nets in a design may be designated as critical.

Long Tracks

Some nets in the design use long tracks. Long tracks are special routing resources that span multiple rows, columns, or modules. Long tracks employ three to five antifuse connections. This increases capacitance and resistance, resulting in longer net delays for macros connected to long tracks. Typically, no more than six percent of nets in a fully utilized device require long tracks. Long tracks contribute approximately 4 ns to 8.4 ns delay. This additional delay is represented statistically in higher fanout routing delays.

Timing Derating

eX devices are manufactured with a CMOS process. Therefore, device performance varies according to temperature, voltage, and process changes. Minimum timing parameters reflect maximum operating voltage, minimum operating temperature, and best-case processing. Maximum timing parameters reflect minimum operating voltage, maximum operating temperature, and worst-case processing.

Temperature and Voltage Derating Factors

Table 1-16 • Temperature and Voltage Derating Factors
(Normalized to Worst-Case Commercial, T_J = 70°C, VCCA = 2.3V)

	Junction Temperature (T _J)						
VCCA	-55	-40	0	25	70	85	125
2.3	0.79	0.80	0.87	0.88	1.00	1.04	1.13
2.5	0.74	0.74	0.81	0.83	0.93	0.97	1.06
2.7	0.69	0.70	0.76	0.78	0.88	0.91	1.00

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eX Family Timing Characteristics

Table 1-17 • eX Family Timing Characteristics (Worst-Case Commercial Conditions, VCCA = 2.3 V, T_J = 70°C)

		−P S	peed	Std Speed		-F Speed		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
C-Cell Propa	agation Delays ¹							
t _{PD}	Internal Array Module		0.7		1.0		1.4	ns
Predicted Ro	outing Delays ²							
t _{DC}	FO=1 Routing Delay, DirectConnect		0.1		0.1		0.2	ns
t _{FC}	FO=1 Routing Delay, FastConnect		0.3		0.5		0.7	ns
t _{RD1}	FO=1 Routing Delay		0.3		0.5		0.7	ns
t _{RD2}	FO=2 Routing Delay		0.4		0.6		8.0	ns
t _{RD3}	FO=3 Routing Delay		0.5		8.0		1.1	ns
t _{RD4}	FO=4 Routing Delay		0.7		1.0		1.3	ns
t _{RD8}	FO=8 Routing Delay		1.2		1.7		2.4	ns
t _{RD12}	FO=12 Routing Delay		1.7		2.5		3.5	ns
R-Cell Timin	g							
t _{RCO}	Sequential Clock-to-Q		0.6		0.9		1.3	ns
t _{CLR}	Asynchronous Clear-to-Q		0.6		8.0		1.2	ns
t _{PRESET}	Asynchronous Preset-to-Q		0.7		0.9		1.3	ns
t _{SUD}	Flip-Flop Data Input Set-Up	0.5		0.7		1.0		ns
t _{HD}	Flip-Flop Data Input Hold	0.0		0.0		0.0		ns
t _{WASYN}	Asynchronous Pulse Width	1.3		1.9		2.6		ns
t _{RECASYN}	Asynchronous Recovery Time	0.3		0.5		0.7		ns
t _{HASYN}	Asynchronous Hold Time	0.3		0.5		0.7		ns
2.5 V Input N	Module Propagation Delays							
t _{INYH}	Input Data Pad-to-Y HIGH		0.6		0.9		1.3	ns
t _{INYL}	Input Data Pad-to-Y LOW		8.0		1.1		1.5	ns
3.3 V Input N	Module Propagation Delays							
t _{INYH}	Input Data Pad-to-Y HIGH		0.7		1.0		1.4	ns
t _{INYL}	Input Data Pad-to-Y LOW		0.9		1.3		1.8	ns
5.0 V Input N	Module Propagation Delays							
t _{INYH}	Input Data Pad-to-Y HIGH		0.7		1.0		1.4	ns
t _{INYL}	Input Data Pad-to-Y LOW		0.9		1.3		1.8	ns
Input Modul	e Predicted Routing Delays ²							
t _{IRD1}	FO=1 Routing Delay		0.3		0.4		0.5	ns
t _{IRD2}	FO=2 Routing Delay		0.4		0.6		8.0	ns
t _{IRD3}	FO=3 Routing Delay		0.5		8.0		1.1	ns
t _{IRD4}	FO=4 Routing Delay		0.7		1.0		1.3	ns
t _{IRD8}	FO=8 Routing Delay		1.2		1.7		2.4	ns
t _{IRD12}	FO=12 Routing Delay		1.7		2.5		3.5	ns

Notes:

^{1.} For dual-module macros, use $t_{PD} + t_{RD1} + t_{PDn}$, $t_{RCO} + t_{RD1} + t_{PDn}$ or $t_{PD1} + t_{RD1} + t_{SUD}$, whichever is appropriate.

2. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance.



Pin Description

CLKA/B Routed Clock A and B

These pins are clock inputs for clock distribution networks. Input levels are compatible with standard TTL or LVTTL specifications. The clock input is buffered prior to clocking the R-cells. If not used, this pin must be set LOW or HIGH on the board. It must not be left floating.

GND Ground

LOW supply voltage.

HCLK Dedicated (Hardwired) Array Clock

This pin is the clock input for sequential modules. Input levels are compatible with standard TTL or LVTTL specifications. This input is directly wired to each R-cell and offers clock speeds independent of the number of R-cells being driven. If not used, this pin must be set LOW or HIGH on the board. It must not be left floating.

I/O Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Based on certain configurations, input and output levels are compatible with standard TTL or LVTTL specifications. Unused I/O pins are automatically tristated by the Designer software.

LP Low Power Pin

Controls the low power mode of the eX devices. The device is placed in the low power mode by connecting the LP pin to logic HIGH. In low power mode, all I/Os are tristated, all input buffers are turned OFF, and the core of the device is turned OFF. To exit the low power mode, the LP pin must be set LOW. The device enters the low power mode 800 ns after the LP pin is driven to a logic HIGH. It will resume normal operation 200 μ s after the LP pin is driven to a logic LOW. LP pin should not be left floating. Under normal operating condition it should be tied to GND via 10 k Ω resistor.

NC No Connection

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

PRA/PRB, I/O Probe A/B

The Probe pin is used to output data from any user-defined design node within the device. This diagnostic pin can be used independently or in conjunction with the other probe pin to allow real-time diagnostic output of any signal path within the device. The Probe pin can be used as a user-defined I/O when verification has been completed. The pin's probe capabilities can be permanently disabled to protect programmed design confidentiality.

TCK, I/O Test Clock

Test clock input for diagnostic probe and device programming. In flexible mode, TCK becomes active when the TMS pin is set LOW (refer to Table 1-4 on page 1-10). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state.

TDI, I/O Test Data Input

Serial input for boundary scan testing and diagnostic probe. In flexible mode, TDI is active when the TMS pin is set LOW (refer to Table 1-4 on page 1-10). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state.

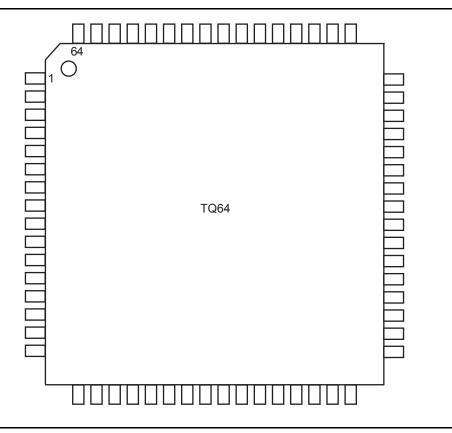
TDO, I/O Test Data Output

Serial output for boundary scan testing. In flexible mode, TDO is active when the TMS pin is set LOW (refer to Table 1-4 on page 1-10). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state. When Silicon Explorer is being used, TDO will act as an output when the "checksum" command is run. It will return to user I/O when "checksum" is complete.



2 – Package Pin Assignments

TQ64



Note: For Package Manufacturing and Environmental information, visit Resource center at www.microsemi.com/soc/products/rescenter/package/index.html.



Datasheet Information

Revision	Changes	Page		
v4.0 (continued)	The "Flexible Mode" section was updated.	1-10		
	Table 1-5 •Boundary-Scan Pin Configurations and Functions is new.			
	The "TRST Pin" section was updated.			
	The "Probing Capabilities" section is new.			
	The "Programming" section was updated.			
	The "Probing Capabilities" section was updated.			
	The "Silicon Explorer II Probe" section was updated.	1-12		
	The "Design Considerations" section was updated.			
	The "Development Tool Support" section was updated.			
	The "Absolute Maximum Ratings*" section was updated.			
	The "Temperature and Voltage Derating Factors" section was updated.			
	The "TDI, I/O Test Data Input" section was updated.			
	The "TDO, I/O Test Data Output" section was updated.			
	The "TMS Test Mode Select" section was updated.			
	The "TRST, I/O Boundary Scan Reset Pin" section was updated.			
	All VSV pins were changed to VCCA. The change affected the following pins:			
	64-Pin TQFP – Pin 36			
	100-Pin TQFP – Pin 57			
	49-Pin CSP – Pin D5			
	128-Pin CSP— Pin H11 and Pin J1 for eX256			
	180-Pin CSP – Pins J12 and K2			
v3.0	The "Recommended Operating Conditions" section has been changed.	1-16		
	The "3.3 V LVTTL Electrical Specifications" section has been updated.			
	The "5.0 V TTL Electrical Specifications" section has been updated.			
	The "Total Dynamic Power (mW)" section is new.			
	The "System Power at 5%, 10%, and 15% Duty Cycle" section is new.			
	The "eX Timing Model" section has been updated.	1-22		
v2.0.1	The I/O Features table, Table 1-2 on page 1-6, was updated.	1-6		
	The table, "Standby Power of eX Devices in LP Mode Typical Conditions, VCCA, VCCI = 2.5 V, TJ = 25° C" section, was updated.			
	"Typical eX Standby Current at 25°C" section is a new table.	1-16		
	The table in the section, "Package Thermal Characteristics" section has been updated for the 49-Pin CSP.			
	The "eX Timing Model" section has been updated.			
	The timing numbers found in, "eX Family Timing Characteristics" section have been updated.			
	The V _{SV} pin has been added to the "Pin Description" section.			
	Please see the following pin tables for the V_{SV} pin and an important footnote including the pin: "TQ64", "TQ100", "128-Pin CSP", and "180-Pin CSP".			
	The figure, "TQ64" section has been updated.	2-1		

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Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "eX Device Status" table on page II, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

Export Administration Regulations (EAR)

The product described in this datasheet is subject to the Export Administration Regulations (EAR). They could require an approved export license prior to export from the United States. An export includes release of product or disclosure of technology to a foreign national inside or outside the United States.

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